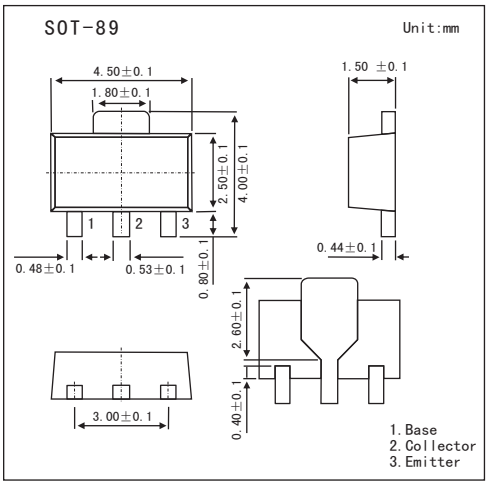
PNP General Purpose Transistors

KTA1662



■ Features

- Small Flat Package.
- Complementary to KTC4374.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-80	V
Collector-emitter voltage	V_{CEO}	-80	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-0.4	A
Collector power dissipation	P_C	500	mW
Jumction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to 150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-1mA,I_E=0	-80			
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-10mA,I_B=0	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-1mA,I_C=0	-5			
Collector cut-off current	I_{CBO}	V_{CB} = -80 V, I_E = 0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB} = -5 V, I_C = 0			-0.1	μA
DC current gain	h_{FE}	V_{CE} = -2 V, I_C = -50mA	70		240	
		V_{CE} = -2 V, I_C = -200m A	40			
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C = -200mA, I_B = -20mA			-0.4	V
Base-emitter voltage	V_{BE}	V_{CE}=-2V,I_C=-5mA			-1.2	V
Transition frequency	f_T	V_{CE}=-10V,I_C=-10mA		120		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz		14		

■ h_{FE} Classification

Marking	FO	FY
Rank	O	Y
Range	70～140	120～240